



PRODUCT RELIABILITY REPORT

Product: MPQ20033-AEC1

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1. Device Information

Product:	MPQ20033-AEC1
Package:	8-PIN QFN (3mm×3mm) 8-PIN QFN (2mm×2mm) 6-PIN THIN QFN (2mm×2mm) 5-PIN TSOT23
Process Technology:	BCD
Report Date:	11/24/2025

2. Summary of Test Results

TEST GROUP A – ACCELERATED ENVIRONMENT STRESS TESTS					
Test	#	Test Condition	Lot# or Date Code	Test Results (S.S./Rej)	Comment
Preconditioning, prior to THB/HAST, AC/UHAST, TC, HTSL and PTC	A1	J-STD-020 Reflow: Tp>=260°C, tp>=30sec, 3×reflows	2508	308/0	QFN3×3-8, MSL=1
			2513	308/0	QFN3×3-8, MSL=1
			2516	308/0	QFN3×3-8, MSL=1
			2513	308/0	QFN2×2-8, MSL=1
			2516	308/0	QFN2×2-8, MSL=1
			2527	308/0	QFN2×2-8, MSL=1
			2439	308/0	TQFN2×2-6, MSL=1
			2510	308/0	TQFN2×2-6, MSL=1
			2527	308/0	TQFN2×2-6, MSL=1
			2503	308/0	TSOT, MSL=1
			2516	308/0	TSOT, MSL=1
			2527	308/0	TSOT, MSL=1
			CSAM@T0	A1	AEC-Q006
2513	22/0	QFN3×3-8			
2516	22/0	QFN3×3-8			
2513	22/0	QFN2×2-8			
2516	22/0	QFN2×2-8			
2527	22/0	QFN2×2-8			
2439	22/0	TQFN2×2-6			
2510	22/0	TQFN2×2-6			
2527	22/0	TQFN2×2-6			
2503	22/0	TSOT			
2516	22/0	TSOT			
2527	22/0	TSOT			
CSAM post-Precondition	A1	AEC-Q006			
			2513	22/0	QFN3×3-8
			2516	22/0	QFN3×3-8
			2513	22/0	QFN2×2-8
			2516	22/0	QFN2×2-8



			2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM pre-HAST	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Highly Accelerated Temperature and Humidity Stress Test (HAST)	A2	JESD22-A110, @130°C/85%RH static bias at Vinmax for 96 hours (1X stress)	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM post-HAST 96hrs (1×Stress)	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT



Ball + Stitch/Wedge Pull post-HAST 96hrs (1×Stress)	A2	AEC-Q006	2508	3/0	QFN3×3-8
			2513	3/0	QFN3×3-8
			2516	3/0	QFN3×3-8
			2513	3/0	QFN2×2-8
			2516	3/0	QFN2×2-8
			2527	3/0	QFN2×2-8
			2439	3/0	TQFN2×2-6
			2510	3/0	TQFN2×2-6
			2527	3/0	TQFN2×2-6
			2503	3/0	TSOT
			2516	3/0	TSOT
			2527	3/0	TSOT
			Ball Shear post-HAST 96hrs (1×Stress)	A2	AEC-Q006
2513	3/0	QFN3×3-8			
2516	3/0	QFN3×3-8			
2513	3/0	QFN2×2-8			
2516	3/0	QFN2×2-8			
2527	3/0	QFN2×2-8			
2439	3/0	TQFN2×2-6			
2510	3/0	TQFN2×2-6			
2527	3/0	TQFN2×2-6			
2503	3/0	TSOT			
2516	3/0	TSOT			
2527	3/0	TSOT			
Cross-section post- HAST 96hrs (1×Stress)	A2	AEC-Q006			
			2513	2/0	QFN3×3-8
			2516	2/0	QFN3×3-8
			2513	2/0	QFN2×2-8
			2516	2/0	QFN2×2-8
			2527	2/0	QFN2×2-8
			2439	2/0	TQFN2×2-6
			2510	2/0	TQFN2×2-6
			2527	2/0	TQFN2×2-6
			2503	2/0	TSOT
			2516	2/0	TSOT
			2527	2/0	TSOT
			Highly Accelerated Temperature and Humidity Stress Test (HAST)	A2	JESD22-A110, @130°C/85%RH static bias at Vinmax for 192 hours (2X stress)
2513	77/0	QFN3×3-8			
2516	77/0	QFN3×3-8			
2513	77/0	QFN2×2-8			
2516	77/0	QFN2×2-8			
2527	77/0	QFN2×2-8			
2439	77/0	TQFN2×2-6			
2510	77/0	TQFN2×2-6			
2527	77/0	TQFN2×2-6			
2503	77/0	TSOT			



			2516 2527	77/0 77/0	TSOT TSOT
CSAM post-HAST 192hrs (2×Stress)	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball + Stitch/Wedge Pull post-HAST 192hrs (2×Stress)	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball Shear post-HAST 192hrs (2×Stress)	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Cross-section post- HAST 192hrs (2×Stress)	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439	1/0 1/0 1/0 1/0 1/0 1/0 1/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6



			2510 2527 2503 2516 2527	1/0 1/0 1/0 1/0 1/0	TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Unbiased Autoclave (AC)/ Unbiased HAST(UHAST)	A3	JESD22-A118, @130°C/85%RH for 192 hours	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM pre-TCC	A2	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Temperature Cycling (TC)	A4	JESD22-A104, from -65°C to 150°C for 500 cycles (1X stress)	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM post-TCC 500cycles (1×Stress)	A4	AEC-Q006	2508 2513 2516 2513	22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8



			2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball + Stitch/Wedge Pull post-TCC 500cycles (1×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball Shear post- TCC 500cycles (1×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0 3/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Cross-section post- TCC 500cycles (1×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT



Temperature Cycling (TC)	A4	JESD22-A104, from -65°C to 150°C for 1000 cycles (2X stress)	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM post-TCC 1000cycles (2×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0 22/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball + Stitch/Wedge Pull post- TCC 1000cycles (2×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Ball Shear post- TCC 1000cycles (2×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503	2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0 2/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT



			2516 2527	2/0 2/0	TSOT TSOT
Cross-section post-TCC 1000cycles (2×Stress)	A4	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
CSAM pre-PTC	A2	AEC-Q006	EPF013	22/0	
Power Temperature Cycling (PTC)	A5	JESD22-A105, from -40°C to 125°C for 1000 cycles (1X stress)	EPF013	45/0	
Power Temperature Cycling (PTC)	A5	JESD22-A105, from -40°C to 125°C for 2000 cycles (2X stress)	EPF013	45/0	
High Temperature Storage Life (HTSL)	A6	JESD22-A103, @175°C for 500 hours (1X stress)	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Cross-section post-HTSL 500hrs (1X stress)	A6	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503	1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT



			2516 2527	1/0 1/0	TSOT TSOT
High Temperature Storage Life (HTSL)	A6	JESD22-A103, @175°C for 1000 hours (2X stress)	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0 77/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT
Cross-section post-HTSL 1000hrs (2X stress)	A6	AEC-Q006	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT

TEST GROUP B – ACCELERATED LIFETIME SIMULATION TESTS

Test	#	Test Condition	Lot# or Date Code	Test Results (S.S./Rej)	Comment
High Temperature Operating Life (HTOL)	B1	JESD22-A108, @Tj=150°C for 1000 hours or equivalent	EPF013 EPF420 EPF12939	77/0 77/0 77/0	
Early Life Failure Rate (ELFR)	B2	AEC-Q100-008, @Tj=150°C for 48 hours, or equivalent	EPF013 EPF420 EPF12939	800/0 800/0 800/0	

TEST GROUP C – PACKAGE ASSEMBLY INTEGRITY TESTS

Test	#	Test Condition	Lot# or Date Code	Test Results (S.S./Rej)	Comment
Wire Bond Shear (WBS)	C1	AEC-Q100-001 AEC-Q003 C _{PK} >1.67 30 bonds from a minimum of 5 devices	2508 2513 2439 2503	5/0 5/0 5/0 5/0	QFN3×3-8 QFN2×2-8 TQFN2×2-6 TSOT



Wire Bond Pull (WBP)	C2	MIL-STD883 Method 2011 AEC-Q003 C _{PK} >1.67 30 bonds from a minimum of 5 devices	2508 2513 2439 2503	5/0 5/0 5/0 5/0	QFN3×3-8 QFN2×2-8 TQFN2×2-6 TSOT
Solderability (SD)	C3	JESD22-B102 J-STD-002D >95% lead coverage	2508 2513 2439 2503	15/0 15/0 15/0 15/0	QFN3×3-8 QFN2×2-8 TQFN2×2-6 TSOT
Physical Dimensions (PD)	C4	JESD22-B100/108 AEC-Q003 C _{PK} >1.67	2508 2513 2516 2513 2516 2527 2439 2510 2527 2503 2516 2527	30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0 30/0	QFN3×3-8 QFN3×3-8 QFN3×3-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 QFN2×2-8 TQFN2×2-6 TQFN2×2-6 TQFN2×2-6 TSOT TSOT TSOT

TEST GROUP D – DIE FABRICATION RELIABILITY TESTS

Test	#	Test Condition	Lot# or Date Code	Test Results (S.S./Rej)	Comment
Electromigration (EM)	D1	JESD61 JP001	—	—	Pass
Time Dependent Dielectric Breakdown (TDDB)	D2	JESD36 JP001	—	—	Pass
Hot Carrier Injection (HCI)	D3	JESD60 and 28 JP001	—	—	Pass
Negative Bias Temperature Instability (NBTI)	D4	JESD90 JP001	—	—	Pass
Stress Migration (SM)	D5	JESD61,87 and 202 JP001	—	—	Pass

TEST GROUP E – ELECTRICAL VERIFICATION TESTS

Test	#	Test Condition	Lot# or Date Code	Test Results (S.S./Rej)	Comment
ESD: Human Body Model (HBM)	E2	AEC-Q100-002	EPF42019	3/0	>2000V
ESD: Device Charged Model (CDM)	E3	AEC-Q100-011	EPF42019	3/0	>750V
Latch-up	E4	AEC-Q100-004	EPF42019	6/0	>+/-100mA & >1.5V _{ccmax}



5. Failure Rate Calculation

Sample Size:	9880
Rejects:	0
Activation Energy (eV):	0.7
Equivalent Device Hours:	7.71×10^8 Hours
Failure Rate (FIT@60%CL):	1.2 FIT
MTBF (years):	96,145 Years

Revision / Update History

<u>Revision</u>	<u>Reason for Change</u>	<u>Date</u>	<u>Rel Engineer</u>
1.0	Initial release	November 2025	Ramon Lei



Appendix: Description of Reliability Test and Failure Rate Calculation

High Temperature Operating Life Test

- Purpose:** This test is used to determine the effects of bias conditions and temperature on solid state devices over time. It simulates the devices operating condition in an accelerated way. The voltage and temperature are used for acceleration of any potential failures over time.
- Condition:** $T_j=150^{\circ}\text{C}$ @ V_{inmax} .
- Pass Criteria:** All units must pass the min/max limits of the datasheet.

ESD Test

- Purpose:** The purpose of the ESD test is to guarantee that the device can withstand electrostatic voltages during handling.
- Condition:** Human Body Model and Charged Device Model.
- Pass Criteria:** ESD Testing on every pin. The device must be fully functional after testing and pass the min/max limits in the datasheet.

IC Latch-Up Test

- Purpose:** The purpose of this specification is to establish a method for determining IC latch-up characteristics and to define latch-up failure criteria. Latch-up characteristics are extremely important in determining product reliability and minimizing No Trouble Found (NTF) and Electrical Overstress (EOS) failures due to latch-up.
- Condition:** Voltage and current injection.
- Pass criteria:** All pins with the exception of “no connect” pins and timing related pins, shall be latch-up tested. The device must be fully functional after testing and pass the min/max limits in the datasheet.

Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices

- Purpose:** The purpose of this standard is to identify the classification level of nonhermetic solid state surface mount devices (SMDs) that are sensitive to moisture-induced stress so that they can be properly packaged, stored, and handled to avoid damage during assembly solder reflow attachment and/or repair operations.
- Condition:** Bake + moisture sock + 3X reflow at 260°C .
- Pass criteria:** All units must pass the min/max limits of the datasheet.

Accelerated Moisture Resistance- Unbiased Autoclave/ Unbiased HAST

- Purpose:** To check the performance of the device in humid environments. This test checks the integrity of the passivation, poor metal to plastic seal and contamination level during assembly and material compatibility.
- Condition:** $121^{\circ}\text{C}/100\% \text{RH}$ (Unbiased Autoclave), $130^{\circ}\text{C}/85\% \text{RH}$ (Unbiased HAST).
- Pass Criteria:** All units must pass min/max limits of the datasheet.

Temperature Cycle Test

- Purpose:** This test is conducted to determine the ability of components and solder interconnects to withstand mechanical stresses induced by alternating high- and low-temperature extremes.
- Condition:** -65°C to 150°C or other conditions.
- Pass Criteria:** All units must pass min/max limits of the datasheet.

Temperature Humidity Bias (THB)/Biased Highly Accelerated Stress Test (BHAST)

- Purpose:** This is to evaluate the reliability in humid environments. Temperature, humidity, and bias conditions are applied to accelerate the penetration of moisture through the external protective material (encapsulant or seal) or along the interface between the external protective material and the metallic conductors which pass through it check the performance of the device in humid environments.
- Condition:** $85^{\circ}\text{C}/85\% \text{RH}$ (THB), $130^{\circ}\text{C}/85\% \text{RH}$ (BHAST), with $V_{in}=V_{inmax}$.
- Pass Criteria:** All units must pass min/max limits of the datasheet.



Power and Temperature Cycling

- Purpose:** This test method applies to semiconductor devices that are subjected to temperature excursions and required to power on and off during all temperatures. The power and temperature cycling test is performed to determine the ability of a device to withstand alternate exposures at high and low temperature extremes with operating biases periodically applied and removed.
- Condition:** -40°C to 125°C, or other condition, with Vin=Vinmax.
- Pass Criteria:** All units must pass min/max limits of the datasheet.

High Temperature Storage Life

- Purpose:** The test is typically used to determine the effects of time and temperature, under storage conditions, for thermally activated failure mechanisms and time-to-failure distributions of solid state electronic devices, including nonvolatile memory devices (data retention failure mechanisms).
- Condition:** Bake at 150°C/175°C or other conditions.
- Pass Criteria:** All units must pass min/max limits of the datasheet.

Failure Rate Calculation

The failure rate is gauged by a Failures-In-Time (FIT) based upon accelerated stress data. The unit for FIT is failure per billion device hour.

$$FIT\ Rate = \frac{(\chi^2/2) \times 10^9}{EDH}$$

Where

- χ^2 (Chi-Squared) is the goodness-of-fit test statistic at a specified level of confidence;
- EDH= Equivalent Device Hours = AF × (Life test sample size) × (test duration);
- AF= Acceleration Factor.

High Temperature Operating Life (HTOL) test is usually done under acceleration of temperature and voltage. The total number of failures from the stress test determines the chi-squared factor.

$$AF = AF_T \times AF_V$$

The Temperature Acceleration Factor AF_T :

$$AF_T = \exp\left(\frac{E_a}{K} \left(\frac{1}{T_{J(Use)}} - \frac{1}{T_{J(stress)}} \right)\right)$$

- T_{Use} = Junction temp under typical operating conditions;
- T_{stress} = Junction temp under accelerated test conditions;
- E_a is Activation energy=0.7eV;
- K =Boltzmann's constant= 8.62×10^{-5} eV/K.

The voltage Acceleration Factor AF_V :

$$AF_V = e^{\beta \times [V_{stress} - V_{use}]}$$

- V_{use} = Voltage under typical operating conditions;
- V_{stress} = Voltage under accelerated stress test conditions;
- β = Voltage acceleration factor (in 1/Volts) and specified by technology.
- Note: For calculation in the report, $AF_V = 1$ for simplicity.

MTBF (Mean Time Between Failure) equals to $10^9/FIT$ (in hours).